



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary (Typ. @ V_{GS} = -4.5V, T_A = +25°C)

V _{DSS}	R _{DS(on)}	Qg	Q_{gd}	l _D
-12V	85mΩ	3.7nC	0.6nC	-2.6A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Battery Management
- Load Switch
- Battery Protection

Features

LD-MOS Technology with the Lowest Figure of Merit:
 R_{DS(Ωn)} = 85mΩ to Minimize On-State Losses

Q_g = 3.7nC for Ultra-Fast Switching

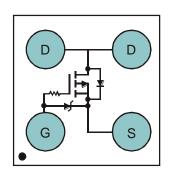
- $V_{gs(th)} = -0.6V$ typ. for a Low Turn-On Potential
- CSP with Footprint 1.0mm × 1.0mm
- Height = 0.62mm for Low Profile
- ESD = 3kV HBM Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: U-WLB1010-4
- Terminal Connections: See Diagram Below
- Weight: 0.005 grams (Approximate)

U-WLB1010-4





Top View Equivalent Circuit

Ordering Information (Note 3)

Part Number	Case	Packaging
DMP1096UCB4-7	U-WLB1010-4	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



1W = Product Type Marking Code YM = Date Code Marking Y = Year (ex: X = 2010) M = Month (ex: 9 = September)



BW = Product Type Marking Code YM = Date Code Marking Y = Year (ex: X = 2010) M = Month (ex: 9 = September)

Date Code Key

Year	2010	20	11	2012	2013	20	14	2015	2016	20	17	2018
Code	Х	`	′	Z	Α	I	3	С	D	E		F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-12	V		
Gate-Source Voltage	V_{GSS}	-5	V		
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-2.6 -2.1	А
Continuous Drain Current (Note 5) V _{GS} = -2.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	-2.4 -1.9	А
Pulsed Drain Current (Note 6)	I _{DM}	-10	А		

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.82	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{\theta JA}$	150	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

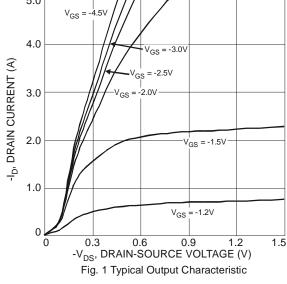
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

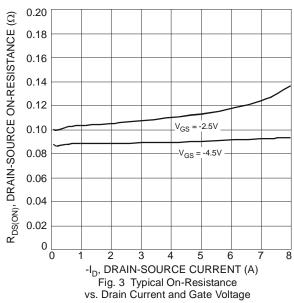
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-12	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$	
Gate-Source Breakdown Voltage	BV _{GSS}	-6.0	-	-	V	$V_{DS} = 0V$, $I_{G} = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	-1	μΑ	$V_{DS} = -9.6V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	-500	nA	$V_{GS} = -5V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(th)}$	-0.4	-0.6	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
		-	85	102		$V_{GS} = -4.5V, I_D = -500mA$	
Static Drain-Source On-Resistance	R _{DS} (ON)	-	97	116	mΩ	$V_{GS} = -2.5V, I_D = -500mA$	
		-	127	152		$V_{GS} = -1.5V, I_D = -500mA$	
Forward Transfer Admittance	Y _{fs}	-	4	-	S	$V_{DS} = -6V, I_{D} = -500mA$	
Diode Forward Voltage	V_{SD}		-0.6	-1.0	V	$V_{GS} = 0V, I_{S} = -500 \text{mA}$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	251	-		N	
Output Capacitance	Coss	-	359	-	pF	$V_{DS} = -6V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	-	70	-		1 = 1.000112	
Total Gate Charge	Q_{g}	-	3.7	-			
Gate-Source Charge	Q_{gs}	-	0.4	-	nC	$V_{GS} = -4.5V, V_{DS} = -6V,$	
Gate-Drain Charge	Q_{gd}	-	0.6	-	IIC	$I_D = -500 \text{mA}$	
Gate Charge at Vth	Q _{g(th)}	-	0.2	-			
Turn-On Delay Time	t _{D(on)}	-	17.6	-			
Turn-On Rise Time	t _r	-	26.9	-		$V_{DS} = -6V, V_{GS} = -2.5V,$	
Turn-Off Delay Time	t _{D(off)}	-	37.5	-	ns	$R_G = 20\Omega$, $I_D = -500 \text{mA}$	
Turn-Off Fall Time	t _f	-	32.3	-			

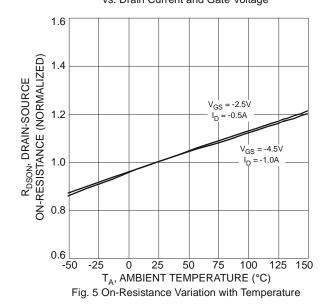
- 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
- Repetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

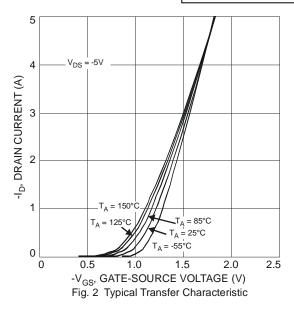


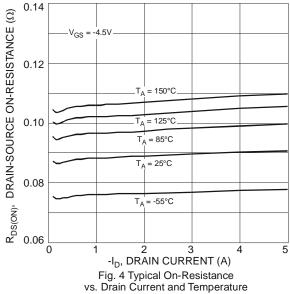












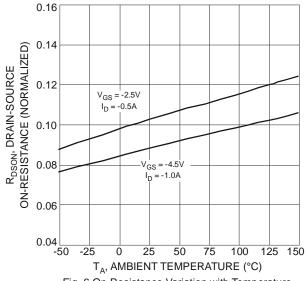


Fig. 6 On-Resistance Variation with Temperature



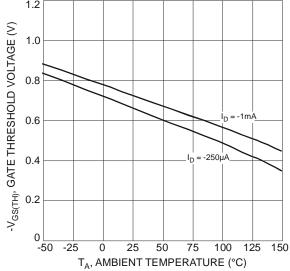
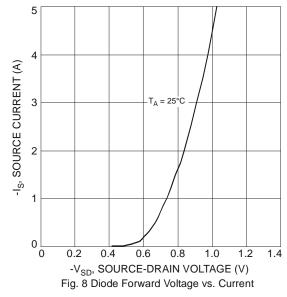
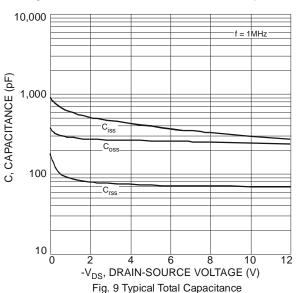


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





1,000

T_A = 150°C

T_A = 125°C

T_A = 85°C

T_A = 25°C

T_A = 25°C

O.01

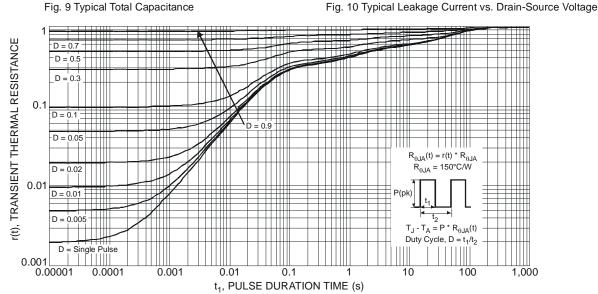
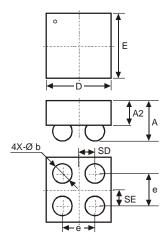


Fig. 11 Transient Thermal Response



Package Outline Dimensions

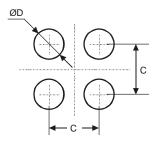
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	U-WLB1010-4						
Dim	Min	Max	Тур				
D	0.95	1.05	1.00				
Е	0.95	1.05	1.00				
Α	-	0.62	_				
A2	_	_	0.38				
b	0.25	0.35	0.30				
е	e – 0.50						
SD	SD 0.25						
SE	SE – – 0.25						
All	All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)	
С	0.50	
D	0.25	



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